

2SD647A 2SD697A

SILICON NPN TRIPLE DIFFUSED MESA TYPE
(DARLINGTON POWER)

INDUSTRIAL APPLICATIONS

Unit in mm

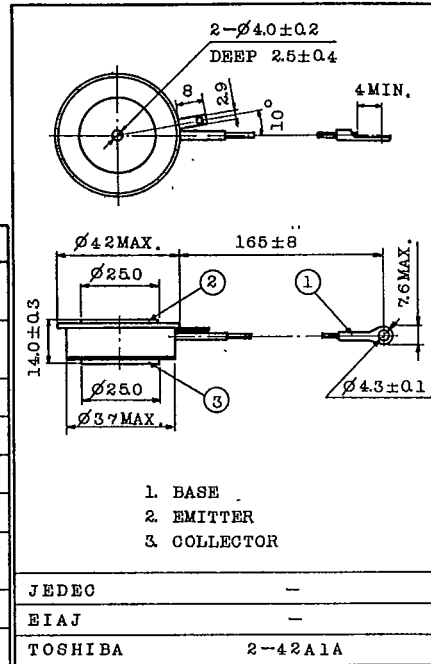
HIGH POWER SWITCHING APPLICATIONS.
DC-AC POWER INVERTER APPLICATIONS.
MOTOR CONTROL APPLICATIONS.

FEATURES:

- High Voltage : $V_{CE(SUS)} \geq 450V$ (2SD697A)
- Triple Diffused Design.
- Darlington Design.

MAXIMUM RATINGS. ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	VCBO	800	V
		500	
Collector-Emitter Voltage	$V_{CE(SUS)}$	600	V
		450	
Emitter-Base Voltage	VEBO	5	V
Collector Current	I_C	100	A
Emitter Current	I_E	-100	A
Base Current	I_B	6	A
Thermal Resistance (Double Side Cooling)	$R_{th(j-c)}$	0.13	$^\circ C/W$
Junction Temperature	T_j	125	$^\circ C$
Storage Temperature Range	T_{stg}	-40 ~ 150	$^\circ C$
Mounting Force Required	F	400±40	kg

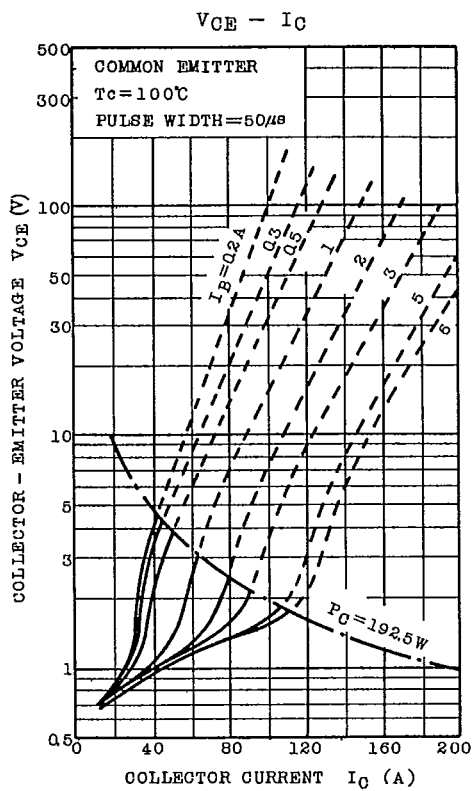
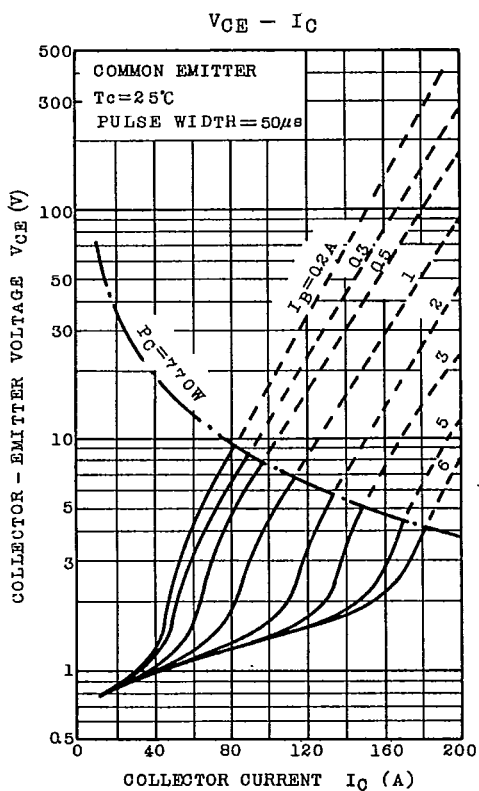
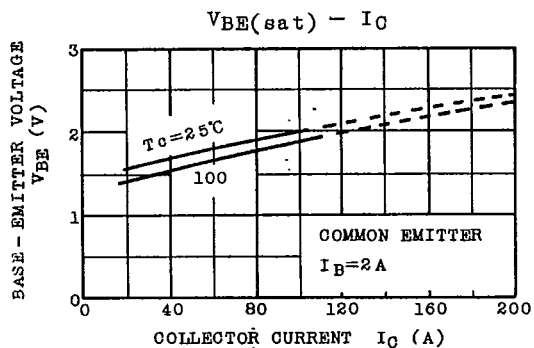


ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

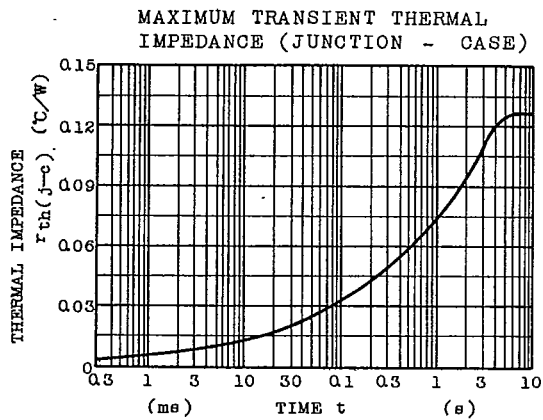
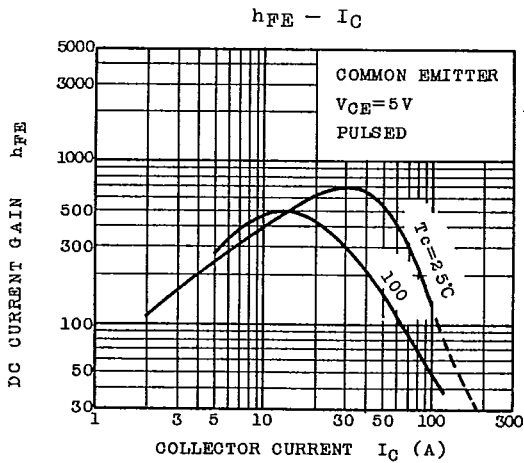
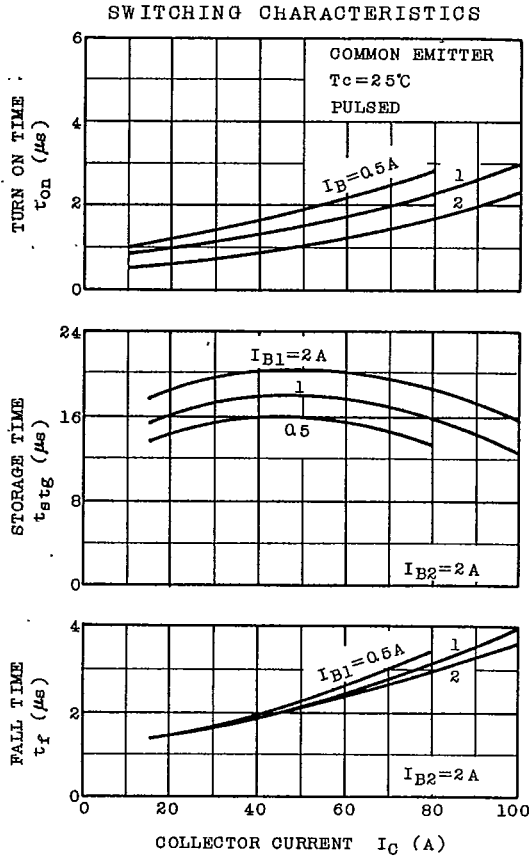
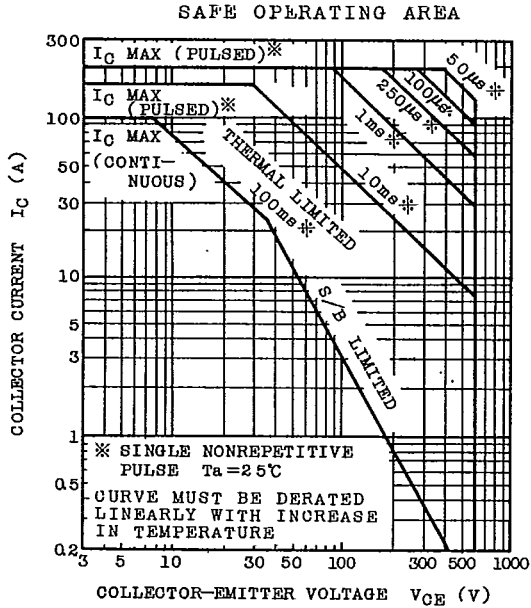
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=100A$	100	-	-	
		$V_{CE}=5V, I_C=50A$	-	500	-	
Collector-Emitter Sustaining Voltage	$V_{CE(SUS)}$	$I_C=0.5A, L=40mH$	600 450	-	-	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100A, I_B=2A$ (Note)	-	-	2.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-	-	2.5	V
Collector Cut-off Current	I_{CBO}	$V_{CB}=800V, I_E=0$	-	-	2	mA
		$V_{CB}=500V, I_E=0$	-	-	2	
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	200	mA
Switching Time	Turn-on Time	$I_C=100A, I_{B1}=2A, I_{B2}=2A, V_C=300V$	-	2.5	-	μs
	Storage Time		-	20	-	μs
	Fall Time		-	4	-	μs

Note : Pulse Test; Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 3\%$
Mounting Force; $F=400kg$

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